



Attorney's Docket No. 07977/088002/US3155D1

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : H. Zhang
Serial No.: 09/362,808
Filed : July 28, 1999
Title : METHOD OF FABRICATING SEMICONDUCTOR DEVICE

Art Unit : 2814
Examiner : Tran, T.

Commissioner for Patents
Washington, D.C. 20231

#8/AMOT
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8/10/01
V. Short

AMENDMENT

Sir:

In response to the Official Action dated March 7, 2001,
Paper No. 2, in the above-referenced application, please amend
the above-identified application as follows.

In the Claims:

Please amend the claims as follows:

1. (Amended) A semiconductor device comprising:
a semiconductor layer having at least channel, source and
drain regions;
an insulating film formed on said semiconductor layer

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CERTIFICATE OF MAILING BY FIRST CLASS MAIL

I hereby certify under 37 CFR §1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated below and is addressed to the Commissioner for Patents, Washington, D.C. 20231.

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